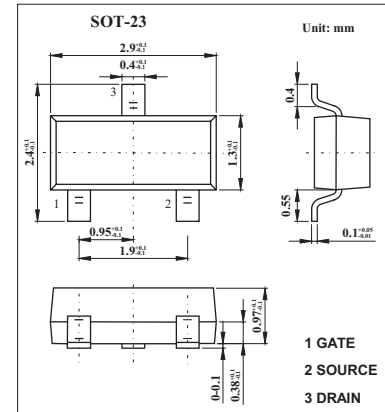


MOS Fied Effect Transistor

2SJ211



■ Features

- Directly driven by Ics having a 5V poer supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the biasresistor.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V _{GS} =0	V _{DSS}	-100	V
Gate to source voltage V _{DS} =0	V _{GSS}	±20	V
Drain current (DC)	I _D	±200	m A
Drain current(pulse) *	I _D	±400	m A
Power dissipation	P _D	200	m W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 ms; d ≤ 50%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-100V, V _{GS} =0			-10	μ A
Gate leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±10	μ A
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-5.0V, I _D =-1 μ A	-1.4	-1.8	-2.4	V
Forward transfer admittance	Y _{fs}	V _{DS} =-5.0V, I _D =-10mA	20	45		ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-4.0V, I _D =-10mA		15	30	Ω
		V _{GS} =-10V, I _D =-10mA		11	20	Ω
Input capacitance	C _{iss}	V _{DS} =-5.0V, V _{GS} =0, f=1MHZ		27		pF
Output capacitance	C _{oss}			16		pF
Reverse transfer capacitance	C _{rss}			2		pF
Turn-on delay time	t _{d(on)}				110	
Rise time	t _r	V _{GS(on)} =-4V, R _G =10 Ω, V _{DD} =-5V, I _D =-10mA RL=500 Ω		150		ns
Turn-off delay time	t _{d(off)}			160		ns
Fall time	t _f			150		ns

■ Marking

Marking	H18
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